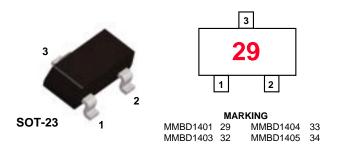
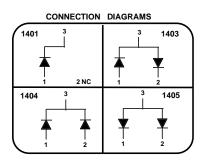


Discrete POWER & Signal **Technologies**

MMBD1401 / 1403 / 1404 / 1405





High Voltage General Purpose Diode

Sourced from Process 1H.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
W _{IV}	Working Inverse Voltage	175	V
Io	Average Rectified Current	200	mA
I _F	DC Forward Current	600	mA
İf	Recurrent Peak Forward Current	700	mA
İf(surge)	Peak Forward Surge Current Pulse width = 1.0 second Pulse width = 1.0 microsecond	1.0 2.0	A A
T _{stg}	Storage Temperature Range	-55 to +150	°C
TJ	Operating Junction Temperature	150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах	Units
		MMBD1401/1403/1404/1405*	
P _D	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

^{*}Device mounted on glass epoxy PCB 1.6" X 1.6" X 0.06"; mounting pad for the collector lead min. 0.93 in2

¹⁾ These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

High Voltage General Purpoise Diode

(continued)

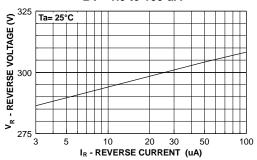
Electrical Characteristics

TA = 25°C unless otherwise noted

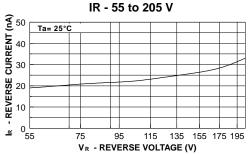
Symbol	Parameter	Test Conditions	Min	Max	Units
B _V	Breakdown Voltage	$I_R = 100 \mu A$	200		V
I _R	Reverse Current	V _R = 120 V V _R = 175 V		40 100	nA nA
V _F	Forward Voltage	I _F = 10 mA I _F = 50 mA I _F = 200 mA I _F = 300 mA	760	800 920 1.0 1.1	mV mV V
Co	Diode Capacitance	V _R = 0, f = 1.0 MHz		2.0	pF
T _{RR}	Reverse Recovery Time	$I_F = I_R = 30 \text{ mA},$ $I_{RR} = 1.0 \text{ mA}, R_L = 100\Omega$		50	nS

Typical Characteristics

REVERSE VOLTAGE vs REVERSE CURRENT BV - 1.0 to 100 uA

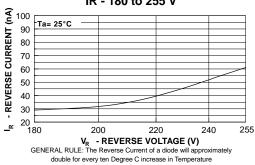


REVERSE CURRENT VS REVERSE VOLTAGE

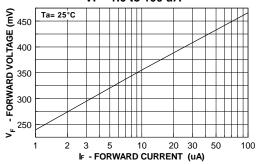


GENERAL RULE: The Reverse Current of a diode will approximately double for every ten (10) Degree C increase in Temperature

REVERSE CURRENT vs REVERSE VOLTAGE IR - 180 to 255 V



FORWARD VOLTAGE vs FORWARD CURRENT VF - 1.0 to 100 uA

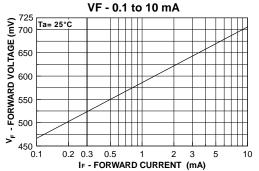


High Voltage General Purpoise Diode

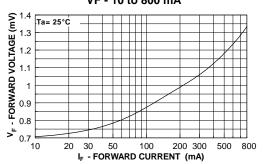
(continued)

Typical Characteristics (continued)

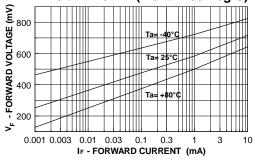
FORWARD VOLTAGE vs FORWARD CURRENT



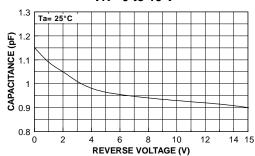
FORWARD VOLTAGE vs FORWARD CURRENT VF - 10 to 800 mA



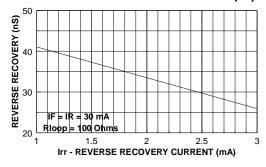
Forward Voltage vs Ambient Temperature VF - 1.0 uA - 10 mA (-40 to + 80 Deg C)



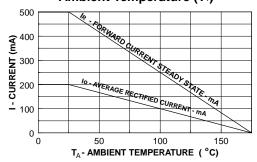
CAPACITANCE vs REVERSE VOLTAGE VR - 0 to 15 V



REVERSE RECOVERY TIME vs REVERSE RECOVERY CURRENT (Irr)



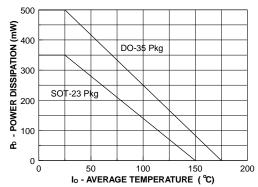
Average Rectified Current (Io) & Forward Current (I_F) versus Ambient Temperature (T_A)



High Voltage General Purpose Diode (continued)

Typical Characteristics (continued)





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PRODUCT STATUS DEFINITIONS

Definition of Terms

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